

processing. Various processes, such as physical vapor deposition (PVD), chemical vapor deposition (CVD), etch, can be performed in the process chambers 12.

Paragraph beginning at line 4 of page 19 has been amended as follows:

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cont
The substrate handler 127 can enter the loadlock chamber 124 at the same time as another substrate handler 112 (shown in Figure 3A) since the loadlock is at atmosphere for transferring the substrates to the loadlock chamber 124 from the high pressure deposition module 101. The opening in the side 128 of the transfer chamber 126 will have been closed prior to vacuum pumping of the transfer chamber 126 which is done prior to transferring the substrates into the processing chamber 130 for deposition of a capping layer.

IN THE CLAIMS:

Please amend claims 2-8, 10-11, 13-22 and 62-63 and add new claims 64-74 as follows.

2. (Amended) The apparatus of claim 64 further comprising one or more multi-slot cooling stations disposed within the transfer area.
3. (Amended) The apparatus of claim 64 further comprising a vacuum pump in fluid communication with the transfer area.
4. (Amended) The apparatus of claim 64 wherein a vacuum pump is in fluid communication with each of the second plurality of chambers.
5. (Amended) The apparatus of claim 64 wherein each of the second plurality of chambers has two isolated processing regions.
6. (Amended) The apparatus of claim 5 wherein each isolated processing region includes a gas distribution assembly disposed therein and each gas distribution assembly shares process gases from one or more gas sources.
7. (Amended) The apparatus of claim 5 further comprising a remote plasma system having an RF generator connected to each individual processing region.
8. (Amended) The apparatus of claim 5 wherein a remote plasma system is in fluid communication with each individual processing region.